

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13	ali-abbas.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:23
L2	55	yang-ming.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:23
L3	7359	"dual damascene" or (dual adj damascene)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:23
L4	120	(ARC or "antireflective") same "etch stop" same trenches	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:24
L5	493	(ARC or "antireflective") and "etch stop" and trenches and (copper or Cu)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:24
L6	1658	(ARC or "antireflective" or SiON) and ("etch stop" or SiN or "silicon nitride" or SiC) and trenches and (copper or Cu)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:27
L7	722	3 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:25
L8	703	7 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:25
L9	294	(ARC or "antireflective" or SiON) same ("etch stop" or SiN or "silicon nitride" or SiC) same (trenches or groove) and (copper or Cu)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:26
L10	1452	(ARC or "antireflective" or SiON or BARC) and ("etch stop" or SiN or "silicon nitride" or SiC) and trenches and (copper or Cu) and (resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:28

L11	710	10 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:28
L12	561	11 and "438"/\$.cccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:28